MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

ESDA14V2L-MS

Product specification



MSKSEMI SEMICONDUCTOR

Features

- 150 Watts peak pulse power (tp = 8/20μs)
- Unidirectional and unidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Protection two data lines:
- IEC 61000-4-2 ±8kV contact ±15kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 10A (8/20μs)

Application

- Dataline
- Automatic Teller Machines
- Net works
- Power line

Mechanical Data

- SOT-23 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Reference News

PACKAGE OUTLINE S	Schematic&PINConfiguratio	Marking
SOT-23		EL15



Absolute Maximum Rating

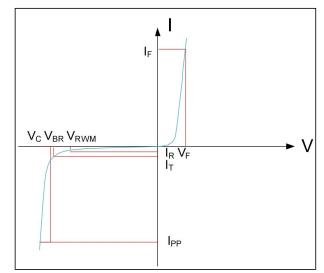
Rating	Symbol	Value	Units
Peak Pulse Power ($t_p=8/20\mu s$)	Р _{РР}	150	Watts
Peak Pulse Current ($t_p=8/20\mu s$) (note1)	Ipp	10	А
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	15 8	kV
Lead Soldering Temperature	TL	260(10seconds)	°C
Junction Temperature	TJ	-55 to + 125	°C
Storage Temperature	T _{stg}	-55 to + 125	°C

Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V _{RWM}				14	V
Reverse Breakdown Voltage	V _{BR}	I _T =1mA	16			V
Reverse Leakage Current	I _R	V _{RWM} =5V,T=25C			1.0	μΑ
Peak Pulse Current	I _{PP}	tp =8/20µs			5	А
Clamping Voltage	V _C	I _{PP} =10A,t _p =8/20µs			30	v
Junction Capacitance	Cj	$V_R = 0V, f = 1MHz$ (PIN1 to PIN3)			60	pF

Electrical Parameters (TA = 25°C unless otherwise noted)

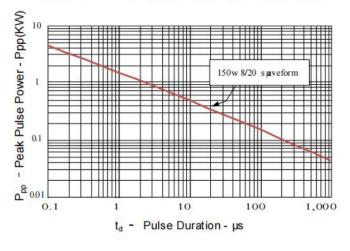
Symbol	Parameter		
РР	Maximum Reverse Peak Pulse Current		
С	Clamping Voltage @ IPP		
RWM	Working Peak Reverse Voltage		
R	Maximum Reverse Leakage Current @ VRWM		
BR	Breakdown Voltage @ IT		
Т	Test Current		





Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time



Percent of Rated Power forlpp Ambient Temperature - T_A (℃)

Figure3: Pulse Waveform

Figure 4: Clamping Voltage vs.lpp

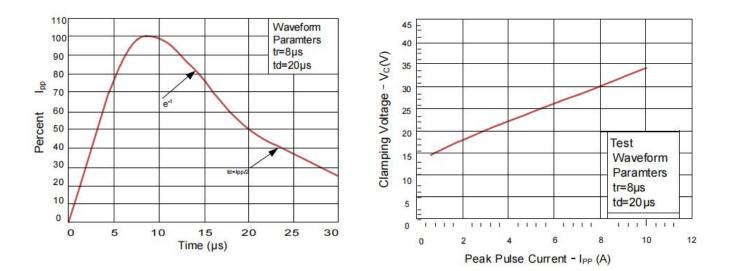
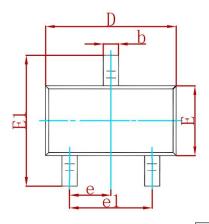
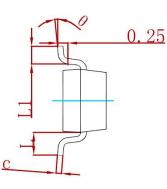


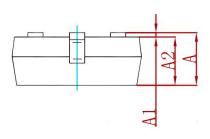
Figure 2: Power Derating Curve



PACKAGE MECHANICAL DATA

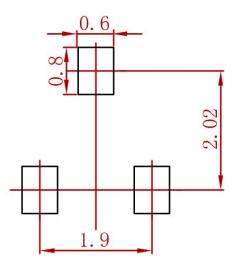






Symbol	Dimensions In Millimeters		Dimensions In Inches	
Symbol	Min	Max	Min	Max
Α	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022	2 REF
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:

1.Controlling dimension: in millimeters.

2.General tolerance:±0.05mm.

3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
ESDA14V2L-MS	SOT-23	3000



Attention

Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.

MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.

Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuits for safedesign, redundant design, and structural design.

■ In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.

■ No part of this publication may be reproduced or transmitted in any form or by any means, electronic or

mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.

Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements intellectual property rights or other rights of third parties.

Any and all information described or contained herein are subject to change without notice due to

product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.

单击下面可查看定价,库存,交付和生命周期等信息

>>MSKSEMI (美森科)